

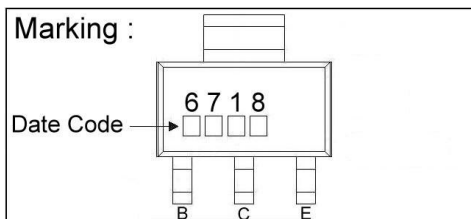
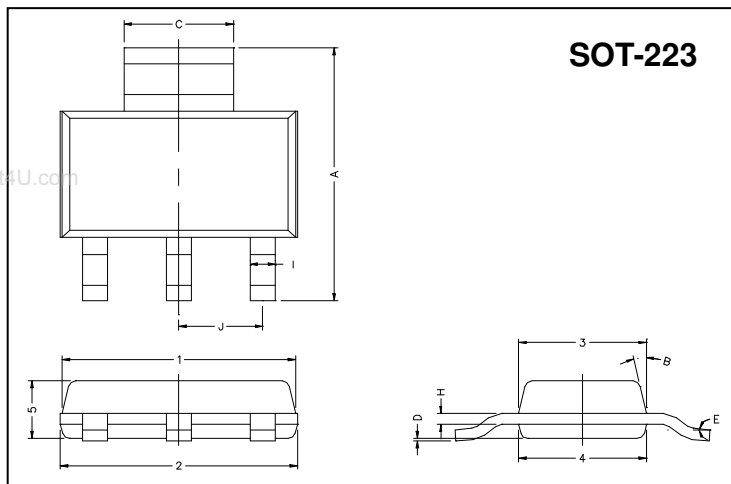
GL6718

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GL6718 is designed for general purpose medium power amplifier and switching.

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13° TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings at Ta = 25°C

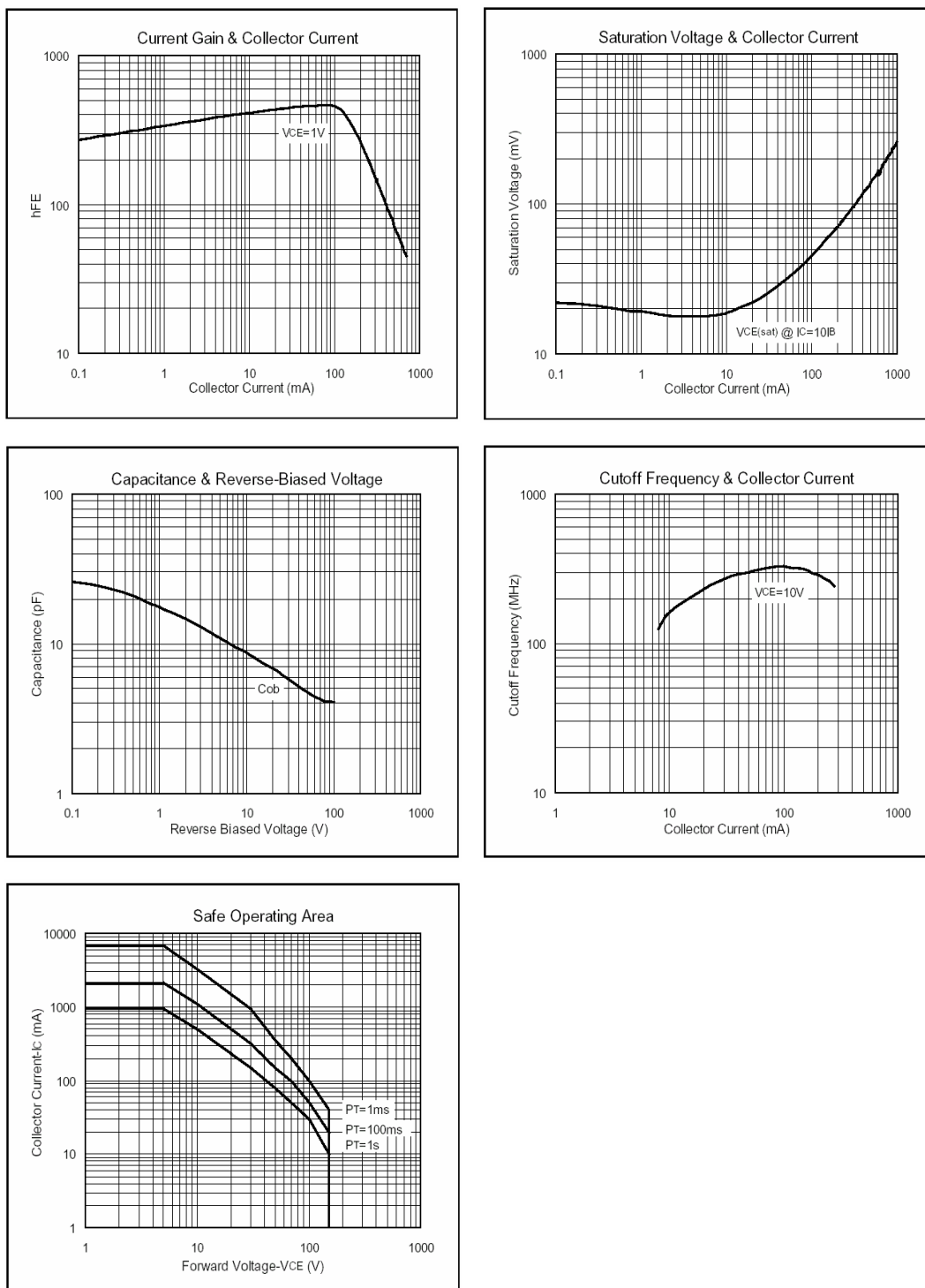
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage at Ta=25°C	VCBO	100	V
Collector to Emitter Voltage at Ta=25°C	VCEO	100	V
Emitter to Base Voltage at Ta=25°C	VEBO	5.0	V
Collector Current at Ta=25°C	IC	1.0	A
Total Power Dissipation at Ta=25°C	PD	1.5	W

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	100	-	-	V	IC=100uA
BVCEO	100	-	-	V	IC=1mA
BVEBO	5	-	-	V	IE=10uA
ICBO	-	-	100	nA	VCB=80V
*VCE(sat)	-	-	350	mV	IC=350Ma, IB=35A
*hFE1	80	-	-		VCE=1V, IC=50mA
*hFE2	100	-	310		VCE=1V, IC=250mA
*hFE2	20	-	-		VCE=1V, IC=500mA
fT	50	-	-	MHz	VCE=10V, IC=50mA, f=100MHz
Cob	-	-	20	pF	VCB=10V, f=1MHz

*Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Characteristics Curve



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